



浩畅半导体
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SD103AW-SD103CW

Schottky Barrier Diode

产品规格书 承认书

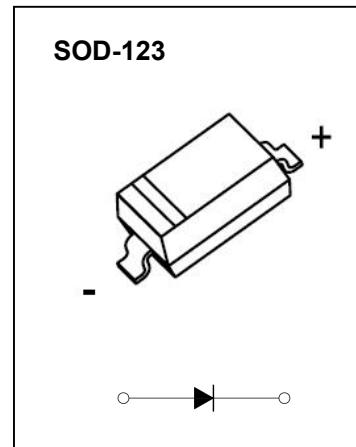
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SOD-123 Plastic-Encapsulate Diodes**SD103AW-SD103CW** Schottky Barrier Diode**FEATURES**

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Capacitance

MARKING:

SD103AW:S4	SD103BW:S5	SD103CW:S6
- S4 +	- S5 +	- S6 +

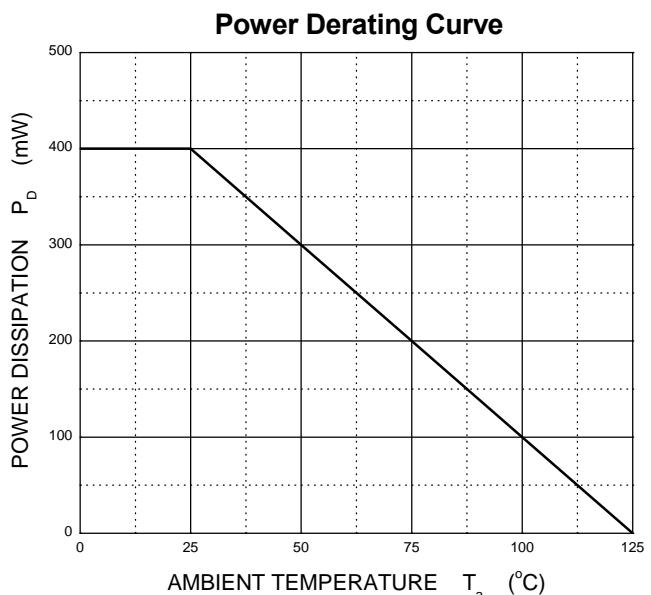
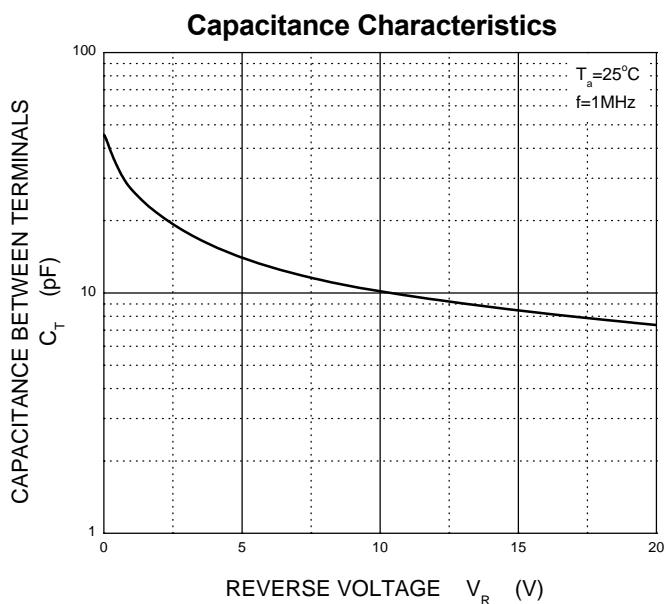
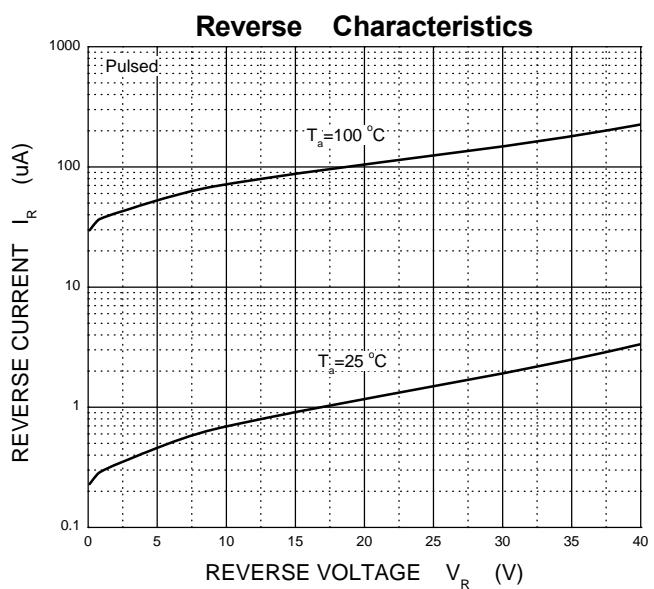
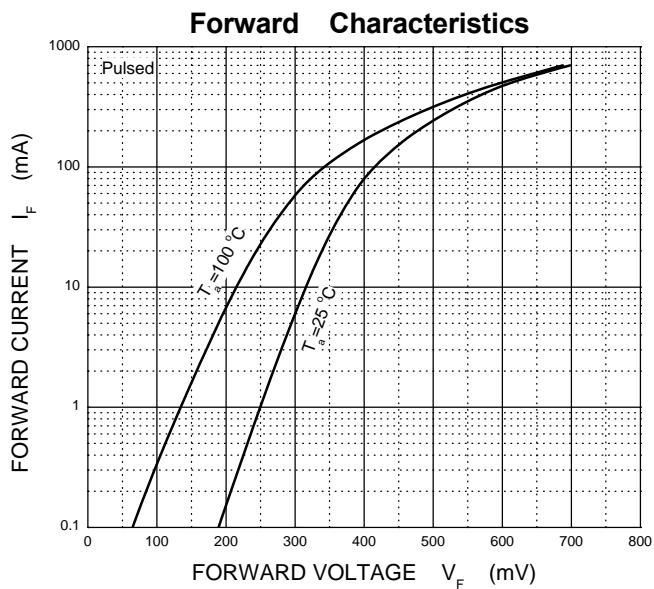
**MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)**

Symbol	Parameter	Value			Unit
		SD103AW	SD103BW	SD103CW	
V_{RPM}	Peak Repetitive Reverse Voltage	40	30	20	V
V_{RWM}	Working Peak Reverse Voltage				
$V_{R(\text{RMS})}$	RMS Reverse Voltage	28	21	14	V
I_{FM}	Forward Continuous Current		350		mA
I_{FSM}	Non-repetitive Peak Forward Surge Current@ $t=8.3\text{ms}$		2		A
P_D	Power Dissipation		400		mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient		250		°C/W
T_j	Junction Temperature		125		°C
T_{stg}	Storage Temperature		-55~+150		°C

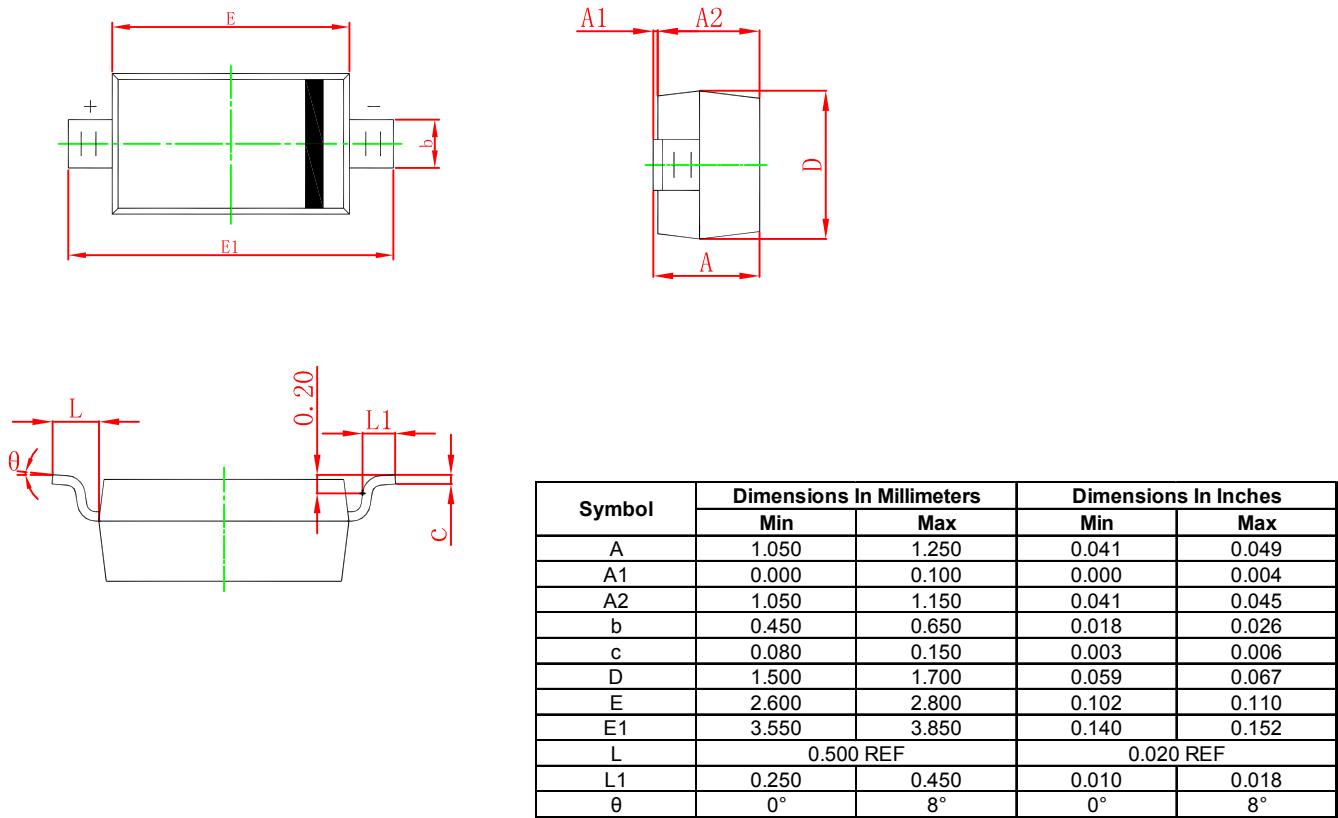
ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	SD103AW	40		V
			SD103BW	30		
			SD103CW	20		
Reverse current	I_R	$V_R=30\text{V}$	SD103AW			μA
		$V_R=20\text{V}$	SD103BW			
		$V_R=10\text{V}$	SD103CW			
Forward voltage	V_F	$I_F=20\text{mA}$			0.37	V
		$I_F=200\text{mA}$			0.6	
Total capacitance	C_{tot}	$V_R=0\text{V}, f=1\text{MHz}$		50		pF
Reverse recovery time	t_{rr}	$I_F=I_R=200\text{mA}, I_{rr}=0.1 \times I_R, R_L=100\Omega$		10		ns

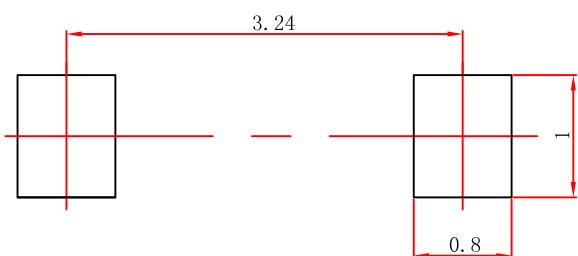
Typical Characteristics



SOD-123 Package Outline Dimensions



SOD-123 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.